

L Number	Hits	Search Text	DB	Time stamp
1	13	czochralski and (noble or inert or argon) near4 mbar	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/20 13:51
2	2	("6291874").PN.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/20 14:11
3	2	("6299892").PN.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/20 15:37
4	3	(zone-drawing or zone adj drawing) near12 czochralski	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/20 16:07
5	6	((("6291874") or ("4330361")).PN.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/20 16:07
-	1154	((257/620) or (438/906) or (437/83) or (437/84) or (117/19) or (117/84)).CCLS.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/20 11:43
-	1	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and (hydrogen with dop\$3 with silicon with wafer) same concentration	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:09
-	90	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and czochralski	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:10
-	18	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and heat adj shield	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:11
-	37	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and nitrogen with dop\$3	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:11
-	43	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and (argon with hydrogen)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:12
-	201	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and oxidation	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:12
-	1	single adj silicon adj crystal.ti,ab. and czochralski.ti,ab. and nitrogen.ti,ab.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:14
-	54	silicon adj single adj crystal.ti,ab. and czochralski.ti,ab. and nitrogen.ti,ab.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:14

		1	method.clm. and silicon.ti,ab. and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:03
		1	silicon.ti,ab. and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:04
		1	silicon and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:05
		1	silicon and (h or hydrogen) and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:06
		1	silicon and (h or hydrogen) and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:06
		1	silicon and (h or hydrogen) and (pressure near5 mbar) and (nitrogen near5 (doping or dopant or doped or dope)) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 18:07
		22	silicon and (h or hydrogen) and pressure and (nitrogen near5 (doping or dopant or doped or dope)) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 19:20
		5	czochralski and pressure near3 mbar and oxygen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 19:21
		23	czochralski.ti,ab. and pressure near3 argon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:37
		5	czochralski.ti,ab. and pressure near3 argon near3 mbar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:37
		0	czochralski.ti,ab. and pressure near3 argon near3 mbar near3 hydrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:38
		3	czochralski.ti,ab. and pressure near3 mbar near3 hydrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:38
		3	czochralski.ti,ab. and pressure near3 mbar near3 hydrogen and silicon.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:39
		3	czochralski.ti,ab. and pressure near3 mbar near3 argon and silicon.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/19 20:39